# MSKSEMI















**ESD** 

TVS

TSS

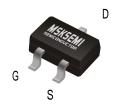
MOV

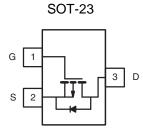
GDT

**PLED** 

# Broduct data sheet







#### **Features**

- -30V, -3.0A,  $RDS(ON) = 150m\Omega@VGS = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

#### **Applications**

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

BVDSS	RDSON	ID
-30V	150m $Ω$	-3.0A

#### Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-30	V
V <sub>G</sub> s	Gate-Source Voltage	±20	V
	Drain Current – Continuous (T <sub>A</sub> =25°C)	-3.0	А
ID .	Drain Current – Continuous (T <sub>A</sub> =70°C)	-2.0	А
I <sub>DM</sub>	Drain Current – Pulsed¹	-12	А
D-	Power Dissipation (T <sub>A</sub> =25°C)	1.56	W
P <sub>D</sub>	Power Dissipation – Derate above 25°C	0.012	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		80	°C/W



#### **Electrical Characteristics** (T<sub>J</sub>=25 °C, unless otherwise noted)

#### **Off Characteristics**

Parameter	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	<b>-</b> 30			V
BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA		<b>-</b> 0.02		V/°C
Drain Source Leakage Current	V <sub>DS</sub> =-27V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			-1	uA
Drain-Source Leakage Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			<b>-</b> 10	uA
Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA

#### **On Characteristics**

D	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-2A		150	190	mΩ
R <sub>DS(ON)</sub>   Static Drain-Source On-Resistance		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1.5A		190	300	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V V I 050 A		<b>-</b> 1.5	<b>-</b> 2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_{D}=-250$ uA		-2.8		mV/°C
gfs	Forward Transconductance	V <sub>DS</sub> =-10V , I <sub>D</sub> =-1A		3		S

#### **Dynamic and switching Characteristics**

Qg	Total Gate Charge <sup>2, 3</sup>			2.5	
$Q_{gs}$	Gate-Source Charge <sup>2, 3</sup>	V <sub>DS</sub> =-24V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-2A		0.1	 nC
$Q_{gd}$	Gate-Drain Charge <sup>2, 3</sup>			1.8	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>			6.1	
Tr	Rise Time <sup>2, 3</sup> $V_{DD}$ =-15V , $V_{GS}$ =-10V , $R_G$ =6 $\Omega$			8.7	 
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>	I <sub>D</sub> =-1A		33.2	 ns
Tf	Fall Time <sup>2,3</sup>			3.7	
C <sub>iss</sub>	Input Capacitance			226	
Coss	Output Capacitance	ut Capacitance V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , F=1MHz		39	 pF
Crss	Reverse Transfer Capacitance			29	
Rg	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz		9.5	 Ω

#### **Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			<b>-</b> 3.0	Α
I <sub>SM</sub>	Pulsed Source Current	VG-VD-UV , FOICE Current			<b>-</b> 6.0	Α
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C			<b>-</b> 1.2	V

#### Note:

- Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%. 3. Essentially independent of operating temperature.



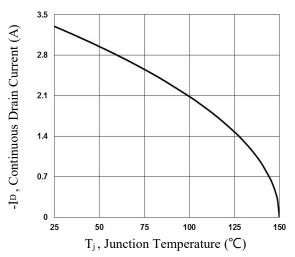


Fig.1 Continuous Drain Current vs. Tc

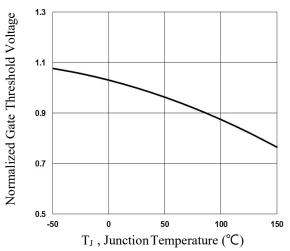


Fig.3 Normalized V<sub>th</sub> vs. T<sub>J</sub>

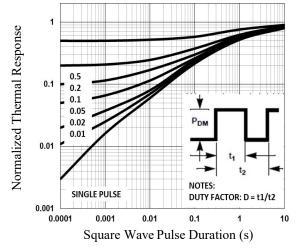


Fig.5 Normalized Transient Impedance

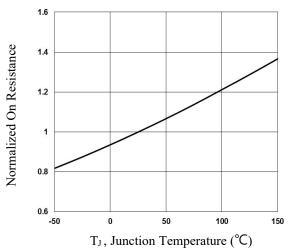


Fig.2 Normalized RDSON vs. T<sub>J</sub>

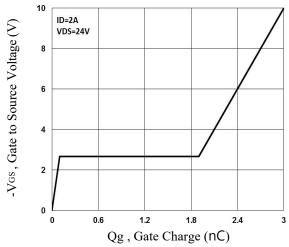


Fig.4 Gate Charge Waveform

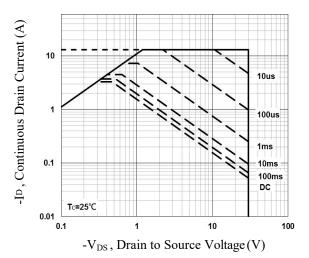
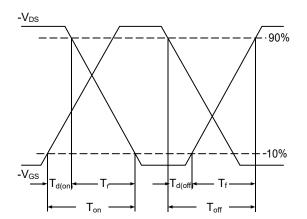


Fig.6 Maximum Safe Operation Area





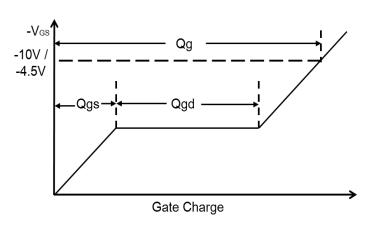
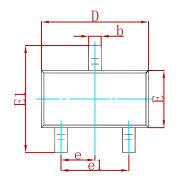


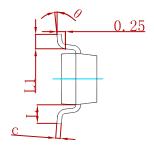
Fig.8 Gate Charge Waveform

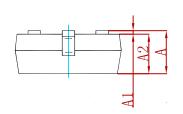






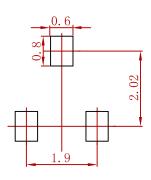






Symbol	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
Е	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.550	REF	0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
SI2303CDS-T1-GE3-MS	SOT-23	3000



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